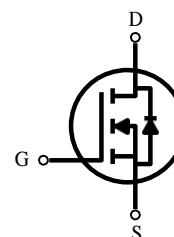
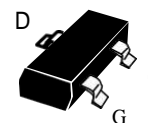


## N-Channel High Density Trench MOSFET

### Features:

- Super high dense cell trench design for low  $R_{DS(on)}$ .
- Rugged and reliable.
- Surface Mount package.
- ESD protected up to 2kv.

SOT-23



### PRODUCT SUMMARY

$V_{DSS}$	$I_D$	$R_{DS(on)}$ (m-ohm) Max
20V	1	280@ $V_{GS} = 4.5V$
	0.7	580@ $V_{GS} = 2.5V$

### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25\text{ }^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	20	V
Gate-Source Voltage	$V_{GS}$	$\pm 8$	V
Drain Current-Continuous <sup>a</sup> @ $T_A = 25\text{ }^\circ\text{C}$ -Pulse <sup>b</sup>	$I_D$	1	A
	$I_{DM}$	4	A
Drain-Source Diode Forward Current <sup>a</sup>	$I_S$	08	A
Maximum Power Dissipation <sup>a</sup>	$P_D$	$T_A = 25\text{ }^\circ\text{C}$	1.25
		$T_A = 75\text{ }^\circ\text{C}$	0.75
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	- 55 to 150	$^\circ\text{C}$

### THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Ambient <sup>a</sup>	$R_{thJA}$	80	$^\circ\text{C/W}$
--	------------	----	--------------------

Note

a. Surface Mounted on FR4 Board,  $t \leq 10\text{sec}$ .

b. Pulse width limited by maximum junction temperature.

**ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C unless otherwise noted)**

Parameter	Symbol	Condition	Min	Typ <sup>c</sup>	Max	Unit
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> = 0V , I <sub>D</sub> = 250uA	20			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 20V , V <sub>GS</sub> = 0V			1	uA
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>GS</sub> = ± 58V , V <sub>DS</sub> = 0V			± 10	uA
<b>ON CHARACTERISTICS<sup>b</sup></b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250uA	0.5	0.7	1	V
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 4.5V , I <sub>D</sub> = 0.8A		280	400	m-ohm
		V <sub>GS</sub> = 2.5V , I <sub>D</sub> = 0.5A		350	500	
Forward Transconductance	g <sub>fs</sub>	V <sub>DS</sub> = 5V , I <sub>D</sub> = 4A		10.7		S
<b>DRAIN-SOURCE DIODE CHARACTERISTICS<sup>b</sup></b>						
Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> = 0V , I <sub>S</sub> = 1.7A			1.2	V
<b>DYNAMIC CHARACTERISTICS<sup>c</sup></b>						
Input Capacitance	C <sub>ISS</sub>	V <sub>DS</sub> = 6V , V <sub>GS</sub> = 0V f = 1.0MHz		480		pF
Output Capacitance	C <sub>OSS</sub>			107		pF
Reverse Transfer Capacitance	C <sub>RSS</sub>			72		pF
<b>SWITCHING CHARACTERISTICS<sup>c</sup></b>						
Turn-On Delay Time	t <sub>D(ON)</sub>	V <sub>DD</sub> = 6V , I <sub>D</sub> = 1A		10.4		ns
Rise Time	t <sub>r</sub>	V <sub>GEN</sub> = 4.5V		3.9		ns
Turn-Off Delay Time	t <sub>D(OFF)</sub>	R <sub>L</sub> = 6 ohm		26		ns
Fall Time	t <sub>f</sub>	R <sub>GEN</sub> = 6 ohm		4.8		ns
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = 6V		4.8		nC
Gate-Source Charge	Q <sub>gs</sub>	I <sub>D</sub> = 2.8A		2.5		nC
Gate-Drain Charge	Q <sub>gd</sub>	V <sub>GS</sub> = 4.5V		0.8		nC

Note

b. Pulse Test Pulse width ≤ 300us , Duty Cycle ≤ 2% .

c. Guaranteed by design , not subject to production testing .

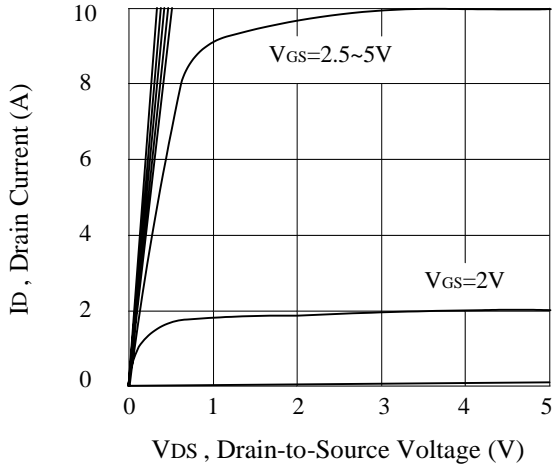


Figure 1. Output Characteristics

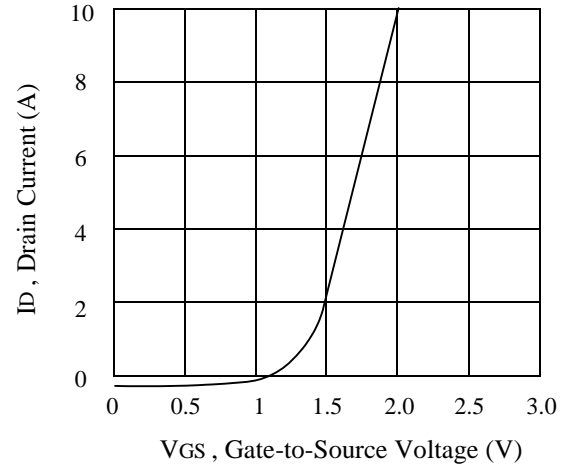


Figure 2. Transfer Characteristics

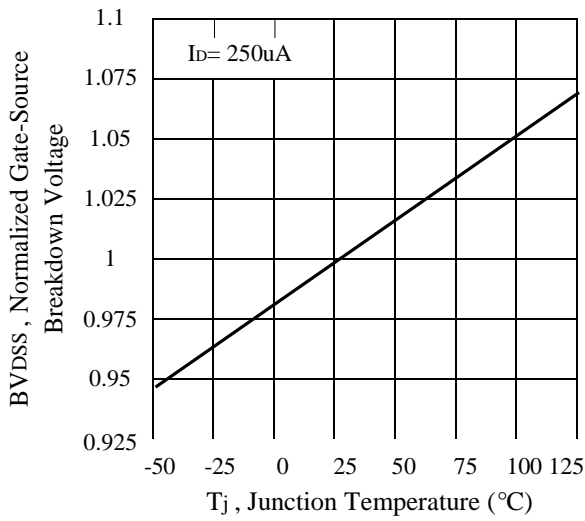


Figure 3. Breakdown Voltage Variation with Temperature

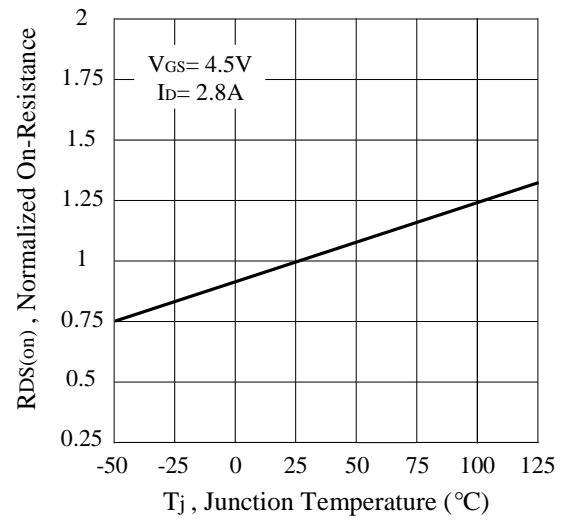


Figure 4. On-Resistance Variation with Temperature

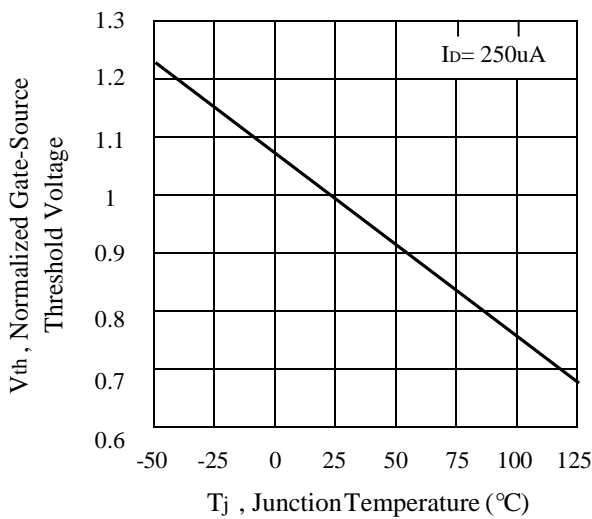


Figure 5. Gate Threshold Variation with Temperature

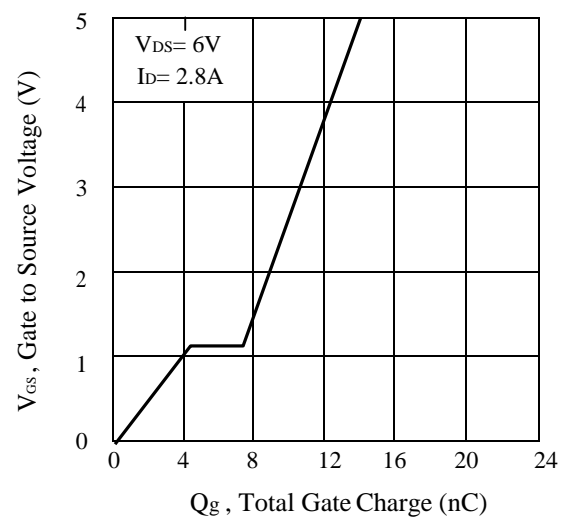


Figure 6. Gate Charge

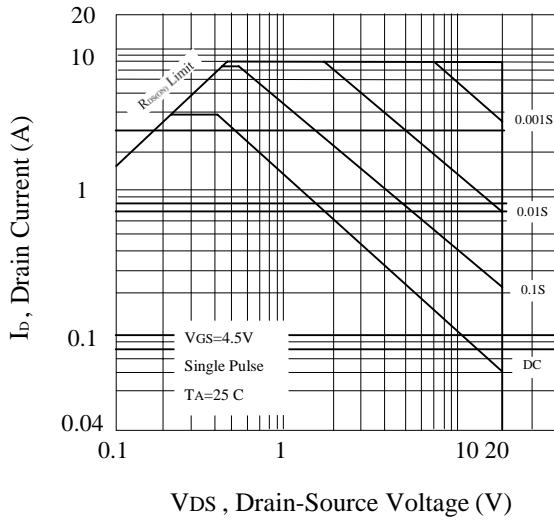


Figure 7. Maximum Safe Operating Area

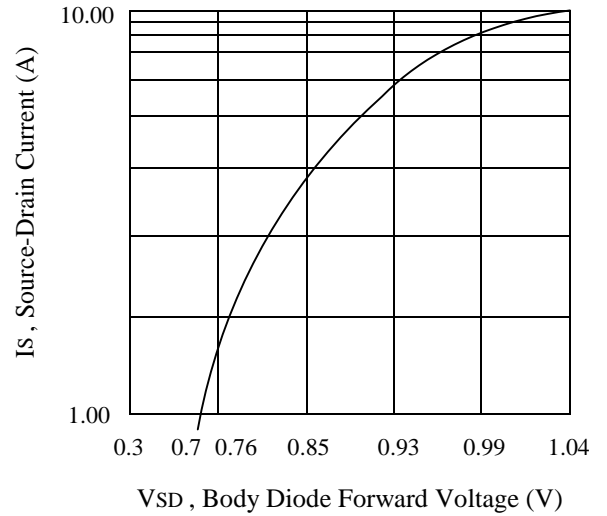


Figure 8. Body Diode Forward Voltage Variation with Source Current

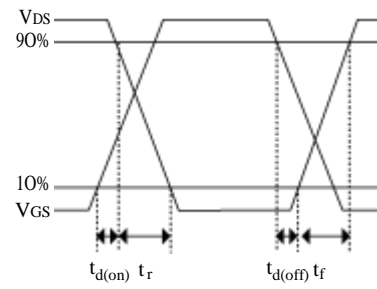
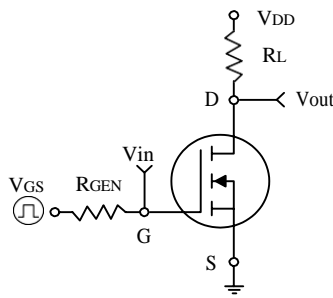


Figure 9. Switching Test Circuit and Switching Waveforms

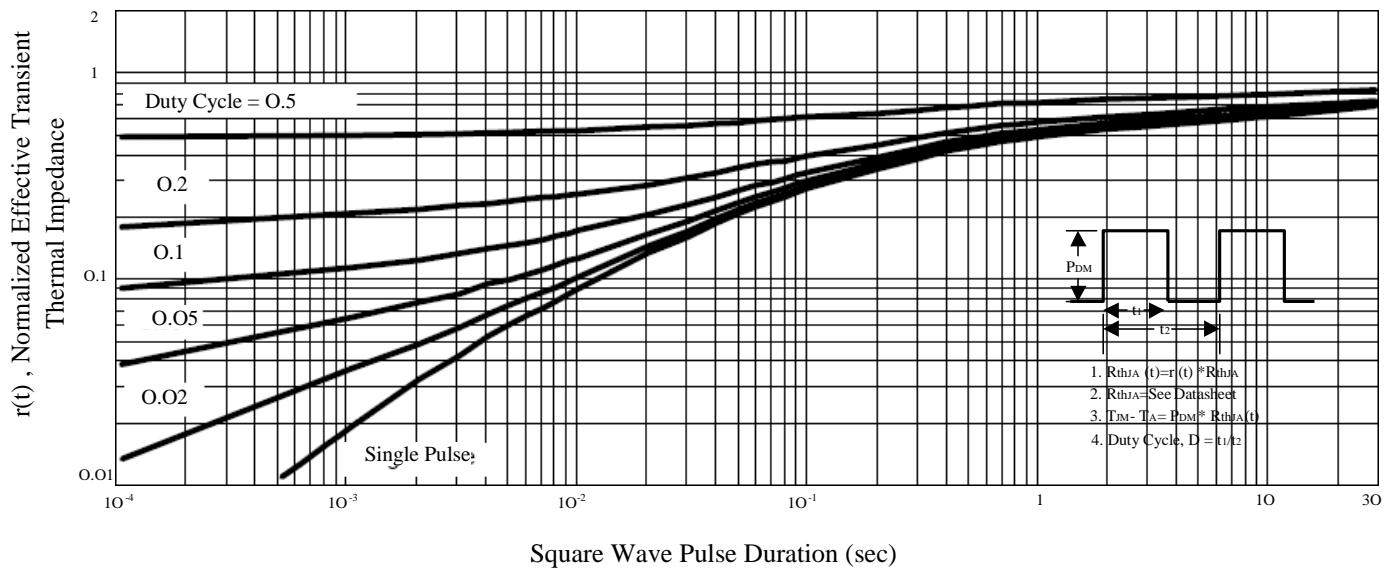


Figure 10. Normalized Thermal Transient Impedance Curve